

DMS05N60

N-Channel Depletion-Mode MOSFET

Features

- Depletion Mode (Normally On)
- Advanced Planar Technology
- Rugged Poly-silicon Gate Cell Structure
- Fast Switching Speed
- ESD Sensitive.
- RoHS compliant package

Applications

- Normally-on Switches
- SMPS start-up Circuit
- Linear Amplifier
- Converters
- Constant Current Source
- Telecom

Package type : SOT-23

Packing & Order Information

3,000/Reel



**RoHS
COMPLIANT**

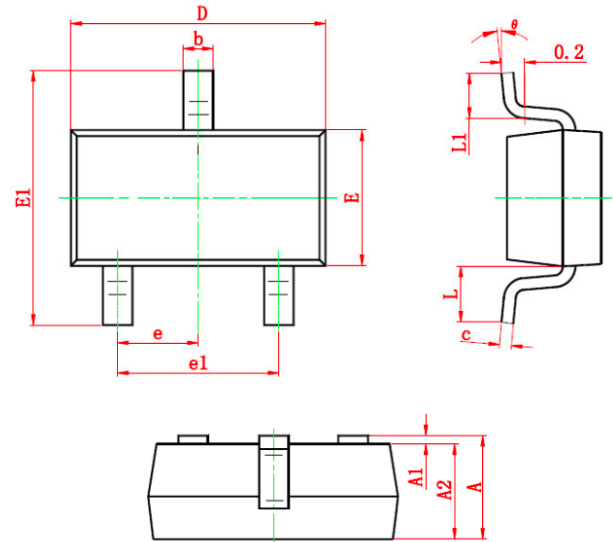
Graphic symbol

drain pin 3

gate
pin 1



source pin 2



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.100	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°

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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings TA=25°C unless otherwise specified

Symbol	Parameter	DMS05N60	Unit
VDSX	Drain-to-Source Voltage ^[1]	600	V
VDGX	Drain-to-Gate Voltage ^[1]	600	V
ID	Continuous Drain Current	0.020	A
IDM	Pulsed Drain Current	0.081	A
PD	Power Dissipation	0.50	W
VGS	Gate-to-Source Voltage	±20	V
TL	Soldering Temperature	300	°C
	Distance of 1.6mm from case for 10 seconds		
TJ, TSTG	Operating and Storage Temperature Range	-55 to +150	

Caution: Stresses greater than those listed in the “Absolute Maximum Ratings “may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	DMS05N60	Unit
RθJA	Thermal Resistance, Junction to Ambient Air	250	K/W

OFF Characteristics TA=25°C unless otherwise specified

Symbol	Parameter	Conditions	Min	Tpy	Max.	Units
BVDSX	Drain-to-Source Breakdown Voltage	VGS=-5V, ID=250μA	600			V
ID(OFF)	Drain-to-Source Teakage Current	VDS=600V, VGS=-5V			0.1	μA
		VDS=600V, VGS=-5V TJ=125°C			10	μA
IGSS	Gate-to-Source Leakage Current	VGS=+20V, VDS=0V			100	nA
		VGS=-20V, VDS=0V			-100	nA

ON Characteristics TA=25°C unless otherwise specified

Symbol	Parameter	Conditions	Min	Tpy	Max.	Units
IDSS	Saturated Drain-to-Source Current	VGS=0V, VDS=25V	12			mA
RDS(ON)	Static Drain-to-Source On-Resistance	VGS=0V, ID=3Ma [4]		500	700	Ω
VGS(OFF)	Gate-to-Source Cut-off Voltage	VDS=3V, ID=8μA	-2.7		-1.5	V
gfs	Forward Transconductance	VDS=10V, ID=5mA		15.4		mS

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Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Conditions	Min	Tpy	Max.	Units
C _{ISS}	Input Capacitance	V _{GS} =-5V		12.3		pf
C _{OSS}	Output Capacitance	V _{DS} =25V		2.6		
C _{RSS}	Reverse Transfer Capacitance	f=1.0MHz		1.8		
Q _g	Total Gate Charge	V _{GS} =-5V~5V V _{DS} =300V, I _D =5mA		1.55		nC
Q _{gs}	Gate-to-Source Charge			0.12		
Q _{gd}	Gate-to-Drain (Miller) Charge			0.56		

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Conditions	Min	Tpy	Max.	Units
T _{d(ON)}	Turn-on Delay Time	V _{GS} =-5V~5V V _{DD} =300V, I _D =5Ma R _G =20Ohm		4		ns
T _{rise}	Rise Time			9		
t _{d(OFF)}	Turn-off Delay Time			14		
t _{fall}	Fall Time			84		

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Conditions	Min	Tpy	Max.	Units
V _{SD}	Diode Forward Voltage	I _{SD} =3.0mA, V _{GS} =-10V			1.2	V

NOTE:

[1] T_J=+25°C to +150°C

[2] Repetitive rating, pulse width limited by maximum junction temperature.

[3] Pulse width ≤ 380 μs ; duty cycle ≤ 2%

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Characteristic Curves

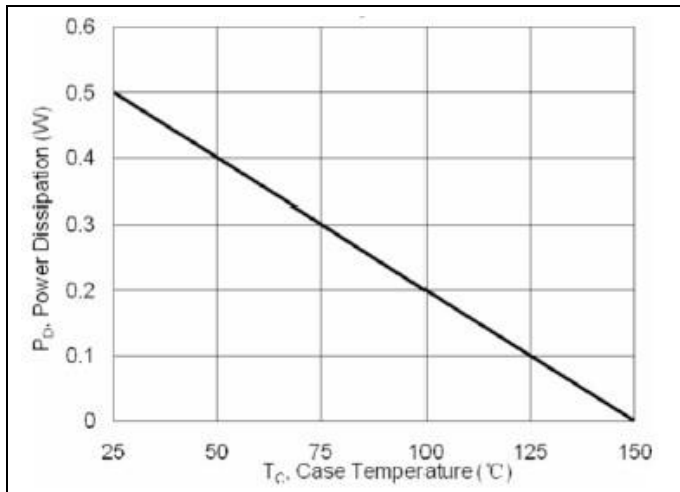


FIG.1 – MAXIMUM POWER DISSIPATION VS CASE TEMPERATURE

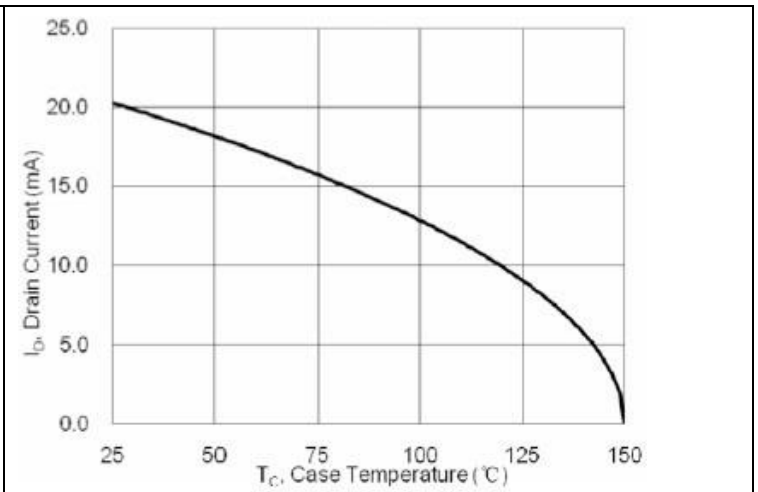


FIG.2 – MAXIMUM CONTINUOUS DRAIN CURRENT VS CASE TEMPERATURE

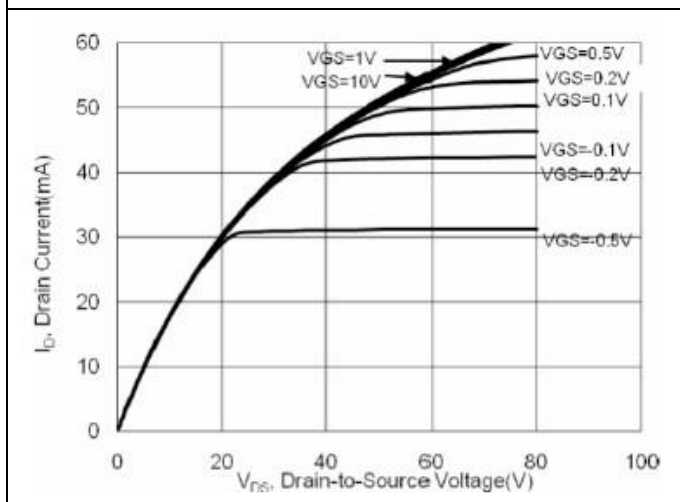


FIG.3 – TYPICAL OUTPUT CHARACTERISTICS

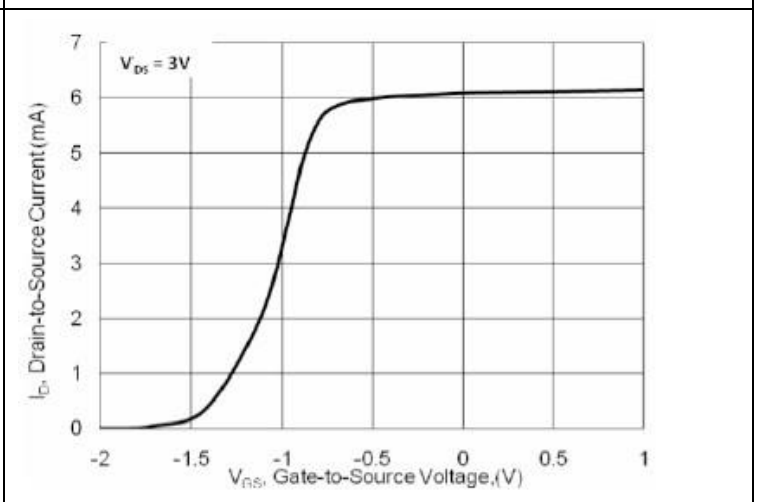


FIG.4 – TYPICAL TRANSFER CHARACTERISTICS

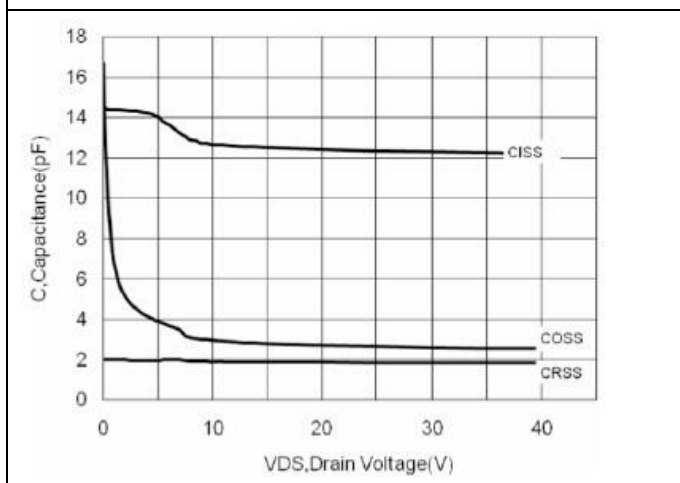


FIG.5 – TYPICAL CAPACITANCE VS. DRAIN-TO-SOURCE VOLTAGE

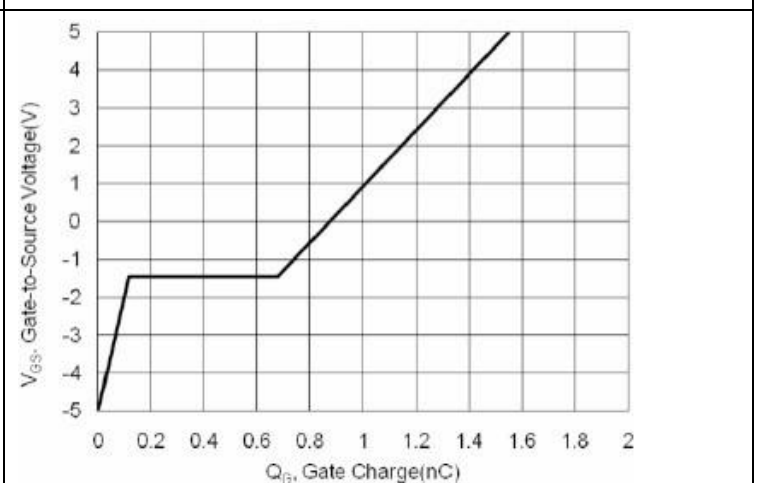


FIG.6 – TYPICAL GATE CHARGE VS GATE-TO-SOURCE VOLTAGE

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